IRFW/I520A

FEATURES

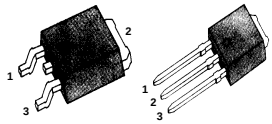
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- 175℃ Operating Temperature
- Lower Leakage Current : 10 μA (Max.) @ V_{DS} = 100V
- Lower $R_{DS(ON)}$: 0.155 Ω(Typ.)

BV_{DSS} = 100 V

$R_{DS(on)}$ = 0.2Ω

I_D = 9.2 A

D²-PAK **I²-PAK**



1. Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	100	V
I_D	Continuous Drain Current (T_C=25℃)	9.2	A
	Continuous Drain Current (T_C=100℃)	6.5	
I_{DM}	Drain Current-Pulsed ①	37	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulsed Avalanche Energy ②	113	mJ
I_{AR}	Avalanche Current ①	9.2	A
E_{AR}	Repetitive Avalanche Energy ①	4.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	6.5	V/ns
P_D	Total Power Dissipation (T_A=25℃) *	3.8	W
	Total Power Dissipation (T_C=25℃)	45	W
	Linear Derating Factor	0.3	W/℃
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +175	℃
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	3.31	℃/W
$R_{\theta JA}$	Junction-to-Ambient *	--	40	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

Electrical Characteristics (T_C=25℃ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	100	--	--	V	V_{GS}=0V,I_D=250μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.12	--	V/℃	I_D=250μA ***See Fig 7***
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=5V,I_D=250μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=100V
		--	--	100		V_{DS}=80V,T_C=150℃
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.2	Ω	V_{GS}=10V,I_D=4.6A ④
g_{fs}	Forward Transconductance	--	6.35	--	Ω	V_{DS}=40V,I_D=4.6A ④
C_{iss}	Input Capacitance	--	370	480	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz ***See Fig 5***
C_{oss}	Output Capacitance	--	95	110		
C_{rss}	Reverse Transfer Capacitance	--	38	45		
$t_{d(on)}$	Turn-On Delay Time	--	14	40	ns	V_{DD}=50V,I_D=9.2A, R_G=18Ω ***See Fig 13*** ④⑤
t_r	Rise Time	--	14	40		
$t_{d(off)}$	Turn-Off Delay Time	--	36	90		
t_f	Fall Time	--	28	70		
Q_g	Total Gate Charge	--	16	22	nC	V_{DS}=80V,V_{GS}=10V, I_D=9.2A ***See Fig 6 & Fig 12*** ④⑤
Q_{gs}	Gate-Source Charge	--	2.7	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	7.8	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	9.2	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	37		
V_{SD}	Diode Forward Voltage ④	--	--	1.5	V	T_J=25℃,I_S=9.2A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	98	--	ns	T_J=25℃,I_F=9.2A di_F/dt=100A/μs ④
Q_{rr}	Reverse Recovery Charge	--	0.34	--	μC	

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
② L=2mH, I_{AS}=9.2A, V_{DD}=25V, R_G=27Ω , Starting T_J=25°C
③ $I_{SD} \leq$ 9.2A, di/dt $\leq$ 300A/μs, $V_{DD} \leq BV_{DSS}$, Starting T_J=25°C
④ Pulse Test : Pulse Width = 250 μs, Duty Cycle $\leq$2%
⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

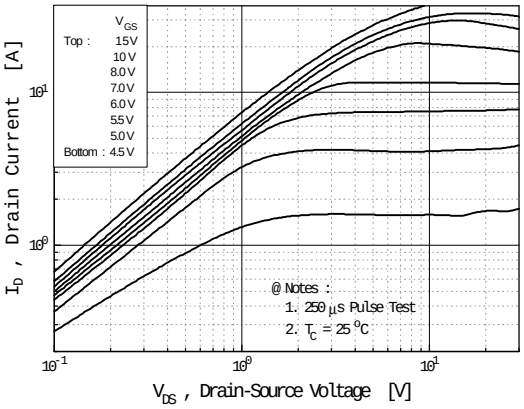


Fig 2. Transfer Characteristics

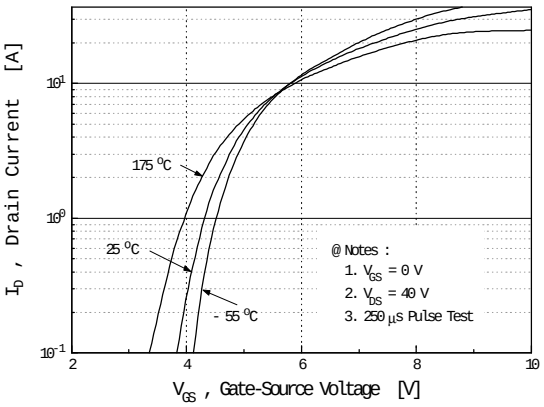


Fig 3. On-Resistance vs. Drain Current

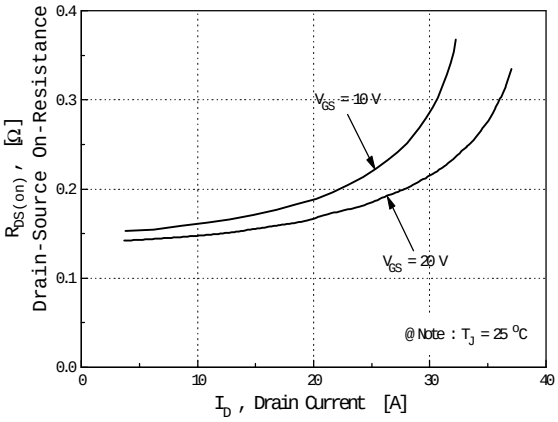


Fig 4. Source-Drain Diode Forward Voltage

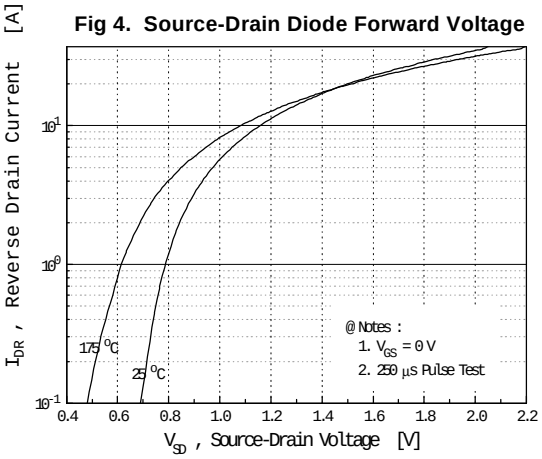


Fig 5. Capacitance vs. Drain-Source Voltage

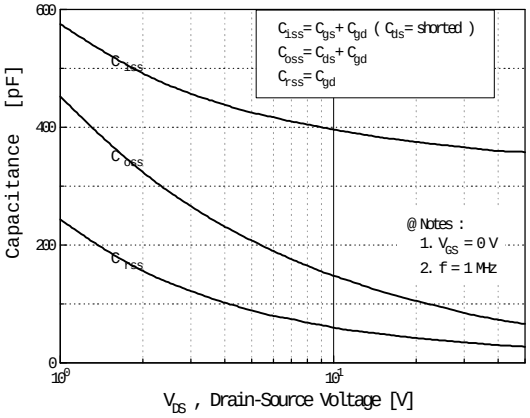


Fig 6. Gate Charge vs. Gate-Source Voltage